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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/982,954	10/22/2001	Gurtej Sandhu	M4065.0353/P353-A	8784	
24998	7590 02/23/2006		EXAM	EXAMINER	
	SHAPIRO MORIN &	MOORE, KARLA A			
2101 L Street, Washington,			ART UNIT	PAPER NUMBER	
,, abi	2000.		1763		

DATE MAILED: 02/23/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
•	09/982,954	SANDHU ET AL.	
Office Action Summary	Examiner	Art Unit	
	Karla Moore	1763	
The MAILING DATE of this communication ap Period for Reply	opears on the cover sheet with t	he correspondence address	•
A SHORTENED STATUTORY PERIOD FOR REPWHICHEVER IS LONGER, FROM THE MAILING I Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication.  If NO period for reply is specified above, the maximum statutory perior Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICAT .136(a). In no event, however, may a reply to d will apply and will expire SIX (6) MONTHS tte, cause the application to become ABAND	TON. De timely filed  from the mailing date of this communic ONED (35 U.S.C. § 133).	
Status			
1)⊠ Responsive to communication(s) filed on 12	December 2005.		
· ·	is action is non-final.		
3) Since this application is in condition for allow	ance except for formal matters,	prosecution as to the merit	ts is
closed in accordance with the practice under	Ex parte Quayle, 1935 C.D. 11	, 453 O.G. 213.	
Disposition of Claims			
4)⊠ Claim(s) <u>1,6-13,16,17 and 46-52</u> is/are pendi	ng in the application.		
4a) Of the above claim(s) is/are withdra	awn from consideration.		
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>1,6-13,16,17 and 46-52</u> is/are reject	ed.		
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction and/	or election requirement.		
Application Papers			
9) The specification is objected to by the Examir	ner.		
10)⊠ The drawing(s) filed on 22 October 2001 is/ar	e: a)⊠ accepted or b)⊡ objec	cted to by the Examiner.	
Applicant may not request that any objection to the	e drawing(s) be held in abeyance.	See 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the corre	ction is required if the drawing(s) is	s objected to. See 37 CFR 1.1	21(d).
11) The oath or declaration is objected to by the E	Examiner. Note the attached Of	fice Action or form PTO-15	2.
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreig a) All b) Some * c) None of:	n priority under 35 U.S.C. § 11	9(a)-(d) or (f).	
1. Certified copies of the priority documer	nts have been received.		
2. Certified copies of the priority documer		cation No	
3. Copies of the certified copies of the pri		_	•
application from the International Burea	au (PCT Rule 17.2(a)).		
* See the attached detailed Office action for a list	at of the certified copies not rece	eived.	
Attachment(s)			
1) Notice of References Cited (PTO-892)	4) Interview Sumn		
<ul> <li>2) Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08</li> </ul>	Paper No(s)/Ma 3) 5) Notice of Inform	nal Patent Application (PTO-152)	
Paper No(s)/Mail Date	6) Other:	,	

U.S. Patent and Trademark Office PTOL-326 (Rev. 7-05) Application/Control Number: 09/982,954 Page 2

Art Unit: 1763

## **DETAILED ACTION**

## Claim Rejections - 35 USC § 112

- 1. The following is a quotation of the second paragraph of 35 U.S.C. 112:
  - The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 2. Claim 52 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. The claim recites the limitation "the vertical inert gas curtain". There is insufficient antecedent basis for this limitation in the claim.

## Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. Claims 1, 6-8, 10-17 and 49 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent No. 5,071,670 to Kelly in view of U.S. Patent No. 5,935,334 to Fong et al.
- 5. Kelly discloses an apparatus *capable* of atomic layer deposition, comprising: a plurality of deposition regions (Figure 1, e1 and e2), each of said regions comprising at least one gas exhaust port (24 and 26), wherein each of said plurality of regions are chemically isolated from one another by vertical inert gas curtains (column 2, rows 64-66 and column 4, rows 41-45), and wherein each of said processes are different from one another; and a central loading robot assembly (104) for moving a first substrate laterally through at least one of said vertical inert gas curtains.
- 6. Examiner notes that although the gas curtains are not explicitly disclosed as vertical, they must be in order to effectively isolate the regions. One of ordinary skill in the art would recognize this.

Art Unit: 1763

- 7. However, Kelly fail to teach a first atomic layer region used for deposition and a second atomic layer region used for thermal diffusion of the dopant species.
- 8. Fong et al. teach deposition of a dopant species in a first processing region and transfer to a second processing region, such as an annealing chamber or a rapid thermal process reactor, for the purpose of driving in the dopant atoms (column 41, row 61 through column 42, 12).
- 9. It would have been obvious to one of ordinary skill in the art at the time the Applicant's invention was made to have provided a first atomic layer doping region for deposition and a second atomic layer doping region for thermal treatment in King in order to diffuse the dopant atoms as taught by Fong et al.
- 10. With respect to claims 6-8, 10-13 and 16-17, similar to the claimed invention, the central loading robot assembly is capable of moving a plurality of substrates laterally through four regions sequentially or in a predefined pattern (see Figures 4A and 4B). Thus, a plurality of substrates can be treated simultaneously in respective pairs of first and second regions and then transferred to another plurality of regions. With respect to each of the regions containing a different processing gas, they are capable as taught at column 7, rows 22-25.
- 11. With respect to claim 49, each of said regions are separate reaction chambers and wherein the reaction chambers are separated by the vertical inert gas curtains.
- 12. Claim 9 is rejected under 35 U.S.C. 103(a) as being unpatentable over Kelly and Fong et al. as applied to claims 1, 6-8, 10-17 and 49 above, and further in view of U.S. Patent No. 6,207,005 B1 to Henley et al.
- 13. Kelly and Fong et al. disclose the invention substantially as claimed and as described above.
- 14. However, Kelly and Fong et al. fail to teach an apparatus comprising a third pair of atomic layer doping regions.
- 15. Henley et al. disclose a deposition apparatus comprising 3 pairs of deposition regions (Figure 1) where increased through put is the result.

Application/Control Number: 09/982,954

Art Unit: 1763

16. It would have been obvious to one of ordinary skill in the art at the time the Applicant's invention was made to have provided an additional pair of deposition regions in Kelly and Fong et al. in order to

Page 4

increase the throughput of the deposition apparatus as taught by Henley et al.

17. Claims 46 and 50 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent No. 5,071,670 to Kelly in view of U.S. Patent No. 5,935,334 to Fong et al. and European Patent Application No. 0 060626 to Gattuso et al.

- 18. Kelly discloses an apparatus *capable* of atomic layer deposition, comprising: a plurality of deposition regions (Figure 1, e1 and e2), each of said regions comprising at least one gas exhaust port (24 and 26), wherein each of said plurality of regions are chemically isolated from one another by vertical inert gas curtains (column 2, rows 64-66 and column 4, rows 41-45), and wherein each of said processes are different from one another; and a central loading robot assembly (104) for moving a first substrate laterally through at least one of said vertical inert gas curtains.
- 19. Examiner notes that although the gas curtains are not explicitly disclosed as vertical, they must be in order to effectively isolate the regions. One of ordinary skill in the art would recognize this.
- 20. However, Kelly fails to teach a first atomic layer region used for deposition and a second atomic layer region used for thermal diffusion of the dopant species.
- 21. Fong et al. teach deposition of a dopant species in a first processing region and transfer to a second processing region, such as an annealing chamber or a rapid thermal process reactor, for the purpose of driving in the dopant atoms (column 41, row 61 through column 42, 12).
- 22. It would have been obvious to one of ordinary skill in the art at the time the Applicant's invention was made to have provided a first atomic layer doping region for deposition and a second atomic layer doping region for thermal treatment in Kelly in order to diffuse the dopant atoms as taught by Fong et al.
- 23. Kelly and Fong et al. disclose the invention substantially as claimed and as described above.
- 24. However, Kelly and Fong et al. to teach an inert gas curtain provided at a higher pressure than said first dopant species.

Application/Control Number: 09/982,954

Art Unit: 1763

25. Gattuso et al. teach the use of an inert gas curtain provided at a pressure somewhat higher than that of the reaction gases within the chamber to create an effective, non-reactive gas curtain (abstract).

Page 5

- 26. It would have been obvious to one of ordinary skill in the art at the time the Applicant's invention was made to have provided an inert gas curtain at a higher pressure than the reaction gases in Kelly and Fong et al. in order to create an effective and non-reactive gas curtain as taught by Gattuso et al.
- 27. With respect to claim 50, each of said regions are separate reaction chambers and wherein the reaction chambers are separated by the vertical inert gas curtains.
- 28. Claims 47 and 51 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent No. 5,071,670 to Kelly in view of U.S. Patent No. 5,935,334 to Fong et al. further in view of U.S. Patent No. 5,382,126 to Hartig et al.
- 29. Kelly discloses an apparatus *capable* of atomic layer deposition, comprising: a plurality of deposition regions (Figure 1, e1 and e2), each of said regions comprising at least one gas exhaust port (24 and 26), wherein each of said plurality of regions are chemically isolated from one another by vertical inert gas curtains (column 2, rows 64-66 and column 4, rows 41-45), and wherein each of said processes are different from one another; and a central loading robot assembly (104) for moving a first substrate laterally through at least one of said vertical inert gas curtains.
- 30. Examiner notes that although the gas curtains are not explicitly disclosed as vertical, they must be in order to effectively isolate the regions. One of ordinary skill in the art would recognize this.
- 31. However, Kelly fails to teach a first atomic layer region used for deposition and a second atomic layer region used for thermal diffusion of the dopant species.
- 32. Fong et al. teach deposition of a dopant species in a first processing region and transfer to a second processing region, such as an annealing chamber or a rapid thermal process reactor, for the purpose of driving in the dopant atoms (column 41, row 61 through column 42, 12).
- 33. It would have been obvious to one of ordinary skill in the art at the time the Applicant's invention was made to have provided a first atomic layer doping region for deposition and a second atomic layer doping region for thermal treatment in Kelly in order to diffuse the dopant atoms as taught by Fong et al.

Art Unit: 1763

- 34. Examiner realizes that the prior art fails to explicitly teach the use of a non-reactive gas in a second region. However, this is seen as an intended use of which the prior art would be capable. The courts have ruled that expressions relating the apparatus to the contents thereof during an intended operation are of no significance in determining the patentability of the apparatus claim. Ex parte Thibault, 164 USPQ 666, 667 (Bd. App. 1969).
- 35. Kelly and Fong et al. disclose the invention substantially as claimed and as described above.
- 36. However, Kelly and Fong et al. fail to teach a separate gas exhaust for each region in a multichamber coating apparatus.
- 37. Hartig et al. teach the use of separate gas exhausts in each chamber for the purpose of aspirating gas from each chamber and further preventing gas transfer between the individual chambers (column 2, rows 17-22).
- 38. It would have been obvious to one of ordinary skill in the art at the time the Applicant's invention was made to have provided separate exhaust mechanisms in each chamber in Kelly and Fong et al. in order to aspirate each chamber and further prevent gas transfer between the individual chambers as taught by Hartig et al.
- 39. With respect to claim 51, each of said regions are separate reaction chambers and wherein the reaction chambers are separated by the vertical inert gas curtains.
- 40. Claim 48 is rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent No. 5,314,538 to Maeda et al. in view of U.S. Patent No. 5,935,334 to Fong et al.
- 41. Maeda et al. disclose a deposition apparatus *capable* of atomic layer deposition, substantially as claimed and comprising, a first deposition region (Figure 2, at "b") for depositing a first gas species on a first substrate as a monolayer, wherein the first deposition region has a first reactive gas supply inlet (38b) located at a first upper position and a first exhaust outlet (40b) connected to a first exhaust system (45b) situated at an opposite position from said first reactive gas supply inlet; a second deposition region (at "c"; also see column 7, rows 20-24) for depositing a second gas species on said first substrate as a monolayer, said first and second deposition regions being chemically isolated from one another by a

Art Unit: 1763

physical barrier having a closeable opening (not shown; column 4, rows 54-57) located between adjacent sidewalls of said first and second deposition regions, wherein the second deposition region has a second

reactive gas supply inlet; and a central loading robot assembly (multiple part numbers; 33 and 34 a-f) for

moving said first substrate from said first deposition region to said second deposition region through said

closeable opening of said physical barrier. Although not explicitly disclosed, the physical barriers would

obviously be oriented vertically in order perform their necessary function of isolation between regions.

42. However, Maeda et al. fail to teach a first atomic layer region used for deposition and a second

atomic layer region used for thermal diffusion of the dopant species.

43. Fong et al. teach deposition of a dopant species in a first processing region and transfer to a

second processing region, such as an annealing chamber or a rapid thermal process reactor, for the

purpose of driving in the dopant atoms (column 41, row 61 through column 42, 12).

44. It would have been obvious to one of ordinary skill in the art at the time the Applicant's invention

was made to have provided a first atomic layer doping region for deposition and a second atomic layer

doping region for thermal treatment in Maeda et al. in order to diffuse the dopant atoms as taught by Fong

et al.

Response to Arguments

45. Applicant's arguments with respect to claims 1, 6-13, 16-17 and 46-52 have been considered but

are moot in view of the new ground(s) of rejection. Each of the claims contains newly added limitations

which are addressed in the rejections above. Applicant's arguments regarding the prior rejections are

obsolete.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should

be directed to Karla Moore whose telephone number is 571.272.1440. The examiner can normally be

reached on Monday-Friday, 9:00 am-6:00 pm.

Application/Control Number: 09/982,954

. Art Unit: 1763

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor,

Page 8

Parviz Hassanzadeh can be reached on 571.272.1435. The fax phone number for the organization

where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application

Information Retrieval (PAIR) system. Status information for published applications may be obtained from

either Private PAIR or Public PAIR. Status information for unpublished applications is available through

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you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC)

at 866-217-9197 (toll-free).

Karla Moore Patent Examiner Art Unit 1763

21 February 2006